

MOS MEMORIES

■ EAROM

Capacity (bit)	Type No.	Organization (words × bits)	Access time max. (ns)	Supply Voltage (V)	Maximum Supply Current		Package	No.	Process	Remarks
					Active (mA)	Standby (μ A)				
32	MN1234	2 × 16	1	+5	165	55	DIP008-P-0300A	M3	Nch MNOS	
256	MN1212A	16 × 16	5	-6.5, -10, -33	230	—	DIP016-P-0300A	M5	Pch MNOS	
272	MN1218A	17 × 16	10	+5, -1, -5, -28	350	—	DIP018-P-0300C	M6	Pch MNOS	
288	MN1224	18 × 16	6	+5, -28	231	—	DIP016-P-0300A	M5	Pch MNOS	
	MN1228	18 × 16	10	+5, -28	231	—	DIP018-P-0300C	M6	Pch MNOS	
304	MN12C28	19 × 16	10	+5	33	1.1	DIP018-P-0300C	M6	CMOSMNOS	
608	MN1219	38 × 16	10	+5, -28	280	—	DIP018-P-0300C	M6	Pch MNOS	
	MN1219S	38 × 16	10	+5, -28	280	—	SOP018-P-0300	M16	Pch MNOS	
	MN1225	38 × 16	6	+5, -28	231	—	DIP016-P-0300A	M5	Pch MNOS	
	MN12C25D	38 × 16	2	+5	33	1.1	SIP009-P-0000	M1	CMOSMNOS	
1k	MN1231	128 × 8	0.45	+5, +22	298	—	DIP014-P-0300A	M4	Nch MNOS	
	MN1220	64 × 16	6	+5, -28	231	—	DIP016-P-0300A	M5	Pch MNOS	
	MN12C20	64 × 16	2	+5	38.5	1.1	SIP009-P-0000	M1	CMOSMNOS	
	MN12201	64 × 16	6	+5, -28	281	—	DIP016-P-0300A	M5	Pch MNOS	With 6-bit latch
	MN12C201D	64 × 16	2	+5	38.5	1.1	DIP016-P-0300A	M5	CMOSMNOS	With 6-bit latch
	MN12C201DS	64 × 16	2	+5	38.5	1.1	SOP018-P-0300	M16	CMOSMNOS	With 6-bit latch
2k	MN1226	128 × 16	6	+5, -28	248	—	DIP016-P-0300A	M5	Pch MNOS	
	MN12261	128 × 16	6	+5, -28	297	—	DIP016-P-0300A	M5	Pch MNOS	With 6-bit latch
	MN12C261D	128 × 16	2	+5	66	1.1	DIP016-P-0300A	M5	CMOSMNOS	With 6-bit latch
	MN12C261DS	128 × 16	2	+5	66	1.1	SOP018-P-0300	M16	CMOSMNOS	With 6-bit latch
4k	MN12C401	256 × 16	0.35	+5	99	1.1	DIP016-P-0300A	M5	CMOSMNOS	With 6-bit latch

Note) MNOS = Metal Nitride Oxide Semiconductor

(Package Symbol) SOP = Small Outline Package, DIP = Dual-In-Line Plastic Package